ESD5102

ESD Protection Diodes

Micro-packaged Diodes for ESD Protection

The ESD5102 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in smartphone, smart-watch, or many other portable / wearable applications where board space comes at a premium.

Features

- Bi-directional Dual Line ESD Protection
- Low Capacitance (5 pF Max, I/O to GND)
- Small Body Outline Dimensions: 0.705 x 0.23 mm
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T_J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	TL	260	°C
IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD)	ESD ESD	±15 ±15	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAM

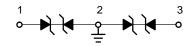


DSN3 CASE 152AW



T = Specific Device CodeM = Month Code

PIN CONFIGURATION AND SCHEMATIC



ORDERING INFORMATION

Device	Package	Shipping [†]
ESD5102FCT5G	DSN3 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

See Application Note AND8308/D for further description of survivability specs.

ESD5102

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V_{BR}	I _T = 1 mA, I/O Pin to GND	3.68	5	6.5	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			0.1	μΑ
Clamping Voltage TLP (Note 1)	V _C	I _{PP} = 8 A		5.4		٧
		I _{PP} = 16 A		6.5		
Junction Capacitance	СЈ	V _R = 0 V, f = 1 MHz			5.5	pF

^{1.} ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50~\Omega$, $t_p = 100~ns$, $t_r = 4~ns$, averaging window; $t_1 = 30~ns$ to $t_2 = 60~ns$.

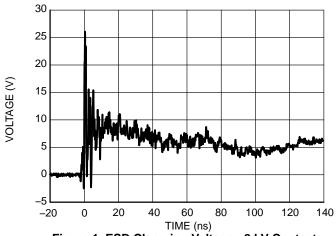


Figure 1. ESD Clamping Voltage +8 kV Contact per IEC61000-4-2

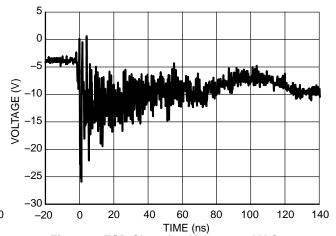
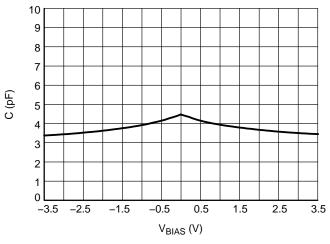


Figure 2. ESD Clamping Voltage –8 kV Contact per IEC61000–4–2

ESD5102

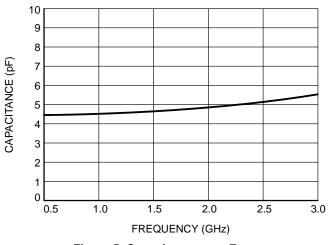
TYPICAL CHARACTERISTICS



2 0 -2 -6 -8 -10 1.E+07 1.E+08 1.E+09 FREQUENCY (Hz)

Figure 3. CV Characteristics

Figure 4. S21 Insertion Loss



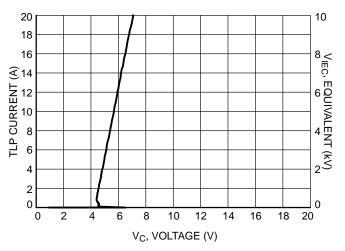


Figure 5. Capacitance over Frequency

Figure 6. Positive TLP I-V Curve

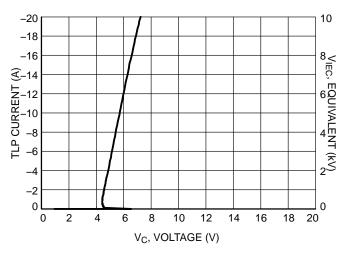


Figure 7. Negative TLP I-V Curve

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

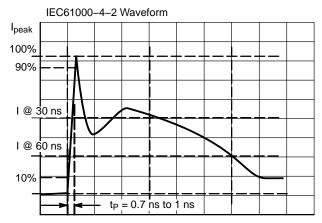


Figure 8. IEC61000-4-2 Spec

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 9. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 10 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

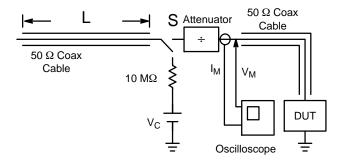


Figure 9. Simplified Schematic of a Typical TLP System

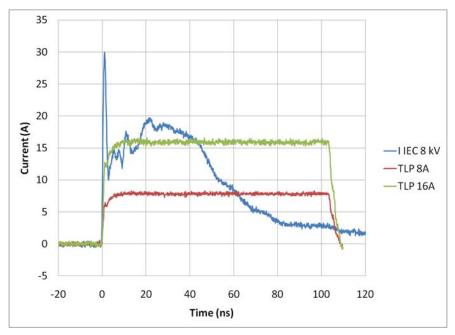
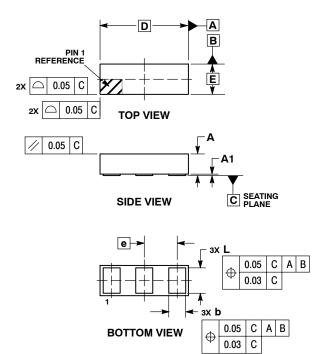


Figure 10. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms



DSN3, 0.73x0.25, 0.27P CASE 152AW **ISSUE O**

DATE 27 MAY 2015



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.13	0.23	
A 1	-	0.03	
b	0.11	0.17	
D	0.73 BSC		
Е	0.25 BSC		
е	0.27 BSC		
L	0.18 0.24		

GENERIC MARKING DIAGRAM*

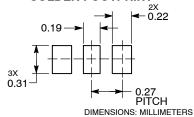


X = Specific Device Code

M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

RECOMMENDED SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DSN3, 0.73X0.25, 0.27P		PAGE 1 OF 1

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